

### **DB-960-90W**

# RF POWER AMPLIFIER using 2 x PD57060S The *LdmosST* FAMILY

PRELIMINARY DATA

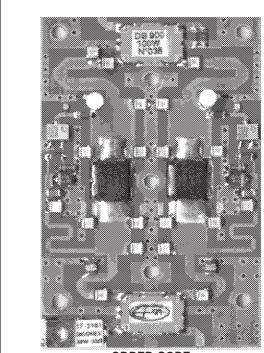
# N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- P<sub>OUT</sub> = 90 W min. with 13 dB gain over 925-960 MHz
- 10:1 LOAD VSWR CAPABILITY
- BeO FREE AMPLIFIER.

#### **DESCRIPTION**

The DB-960-90W is a common source N-Channel enhancement-mode lateral Field-Effect RF power amplifier designed for GSM/GPRS/EDGE base station applications.

The DB-960-90W is designed in cooperation with Europeenne de Telecomunications S.A. (www.et-sa.rf), for high gain and broadband performance operating in common source mode at 26 V, capable of withstanding load mismatch up to 10:1 all phases and with harmonics lower than 30 dBc.



ORDER CODE DB-960-90W

MECHANICAL SPECIFICATION L=80 mm W=50 mm H=10 mm

#### ABSOLUTE MAXIMUM RATINGS (T<sub>CASE</sub> = 25°C)

Symbol	Parameter	Value	Unit
$V_{DD}$	Supply voltage	32	V
I <sub>D</sub>	Drain Current	12	А
P <sub>DISS</sub>	Power Diss. at Tcase = +85°C	145 W	
T <sub>CASE</sub>	Operating Case Temperature	-20 to +85	°C
P <sub>amb</sub>	Max. Ambient Temperature	+55 °C	

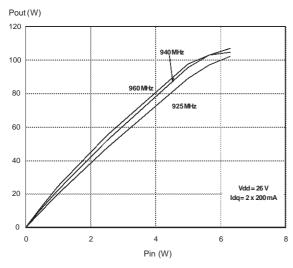
January, 28 2002 1/5

### ELECTRICAL SPECIFICATION (T<sub>amb</sub> = +25°C, Vdd = 26V, Idq = 2 x 200 mA)

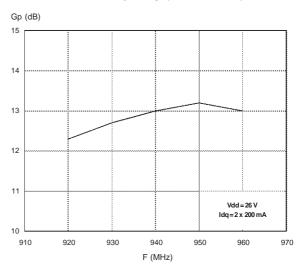
Symbol	Test Conditions	Min.	Тур.	Max.	Unit
FREQ.	Frequency Range	925		960	MHz
Gain	P <sub>OUT</sub> = 90 W	12	13		dB
P <sub>1dB</sub>	Over frequency range: 925 - 960 MHz	90	100		W
Flatness	Over frequency range and @ POUT = 90 W			+/- 0.5	dB
Flatness	Pout from 0.1W to 90 W			1	dB
ND at P <sub>1dB</sub>	P <sub>1dB</sub>	40	45		%
IRTL	Input return Loss P <sub>OUT</sub> from 0.1W to 90 W		-20	-15	dB
Harmonic	Pout = 90 W			-30	dBc
VSWR	Load Mismatch all phases @ Pout = 90 W	10:1			
Spurious	10:1 VSWR all phases and P <sub>OUT</sub> from 0.1 to 90 W			-76	dBc
IMD <sub>3</sub>	Pout = 90 WPEP			-25	dBc

#### TYPICAL PERFORMANCE

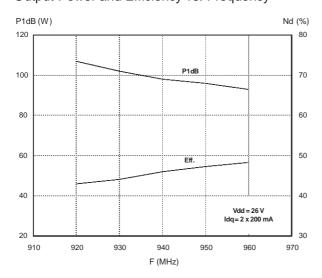
#### Output Power vs. Input Power



#### Power Gain vs. Frequency (Pout = 90W)

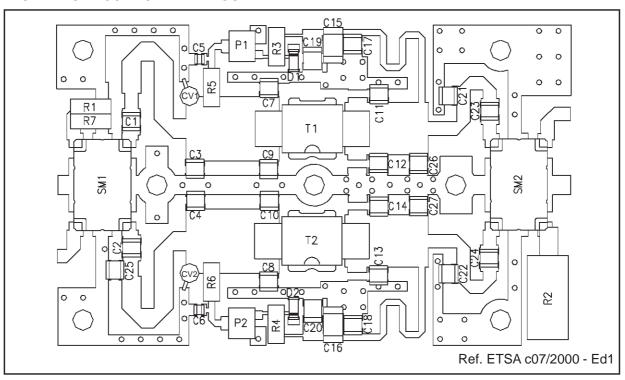


#### Output Power and Efficiency vs. Frequency

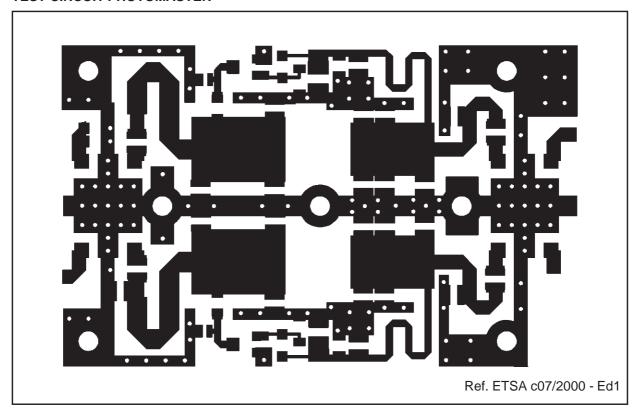


2/5

#### **TEST FIXTURE COMPONENT LAYOUT**



#### **TEST CIRCUIT PHOTOMASTER**



5/

#### DB-960-90W

#### TEST CIRCUIT COMPONENT PART LIST

COMPONENT	DESCRIPTION			
T1, T2	PD57060S TRANSISTOR			
C1, C2, C23, C24	47pF - 500V CERAMIC CHIP CAPACITOR			
C3, C4	3.3pF - 500V CERAMIC CHIP CAPACITOR			
C5, C6, C17, C18	100pF - 500V CERAMIC CHIP CAPACITOR			
C7, C8, C9, C10, C11, C13	10pF - 500V CERAMIC CHIP CAPACITOR			
C12, C14	6.8pF - 500V CERAMIC CHIP CAPACITOR			
C15, C16	100nF - 63V CERAMIC CHIP CAPACITOR			
C19, C20	1μF / 35V ELECTROLYTIC CAPACITOR			
C21, C22, C26, C27	3.3pF - 500V CERAMIC CHIP CAPACITOR			
C25	0.5pF - 500V CERAMIC CHIP CAPACITOR			
CV1, CV2	ADJUSTABLE CAPACITOR 0.6 - 4.5pF / 500V			
P1, P2	10K Ohms MULTITURN POTENTIOMETER			
R1,R7	100 Ohms 1/4W 1206 SMD CHIP RESISTOR			
R2	50 Ohms 30W - 4GHz LOAD			
R3, R4	4.7K Ohms 1/4W 1206 SMD CHIP RESISTOR			
R5, R6	10K Ohms 1/4W 1206 SMD CHIP RESISTOR			
D1, D2	ZENER DIODE 5V - 500 mW SOD80			
SM1, SM2	90° SMD HYBRID COUPLER ANAREN Xinger 1304-3			
BOARD	METCLAD MX3-30-C1/10C THK 0.762 mm Cu 35μ			
SUBSTRATE	TEFLON-GLASS Er = 2.55			
BACK SIDE	COPPER FLANGE 2 mm THICKNESS			
CERAMIC CHIP CAPACITORS	ATC100B or EQUIVALENT			

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics ® 2001 STMicroelectronics - All Rights Reserved

All other names are the property of their respective owners.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

